

SOT-89 Plastic-Encapsulate Transistors

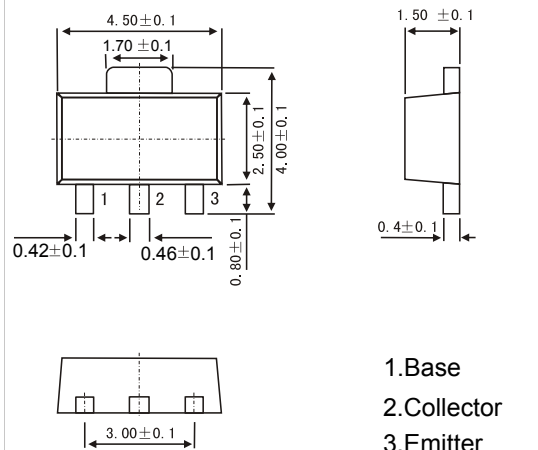
Features

- Low VCE(sat)
- Compliments to 2SB1132
- NPN Transistors

MECHANICAL DATA

- Case style:SOT-89molded plastic
- Mounting position:any

SOT-89



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	V _{CB0}	40	V
Collector-Emitter Voltage	V _{CEO}	32	V
Emitter-Base Voltage	V _{EB0}	5	V
Collector Current (DC) P _w =20ms, duty=1/2	I _c	1 2	A A
Collector Power Dissipation	P _C *	0.5	W
Jumction temperature	T _j	150	°C
Storage temperature Range	T _{stg}	-55 to +150	°C

* mounted on a 40x40x0.7mm ceramic board.

PACKAGE INFORMATION

Device	Package	Shipping
2SD1664	SOT-89	1000/Tape&Reel

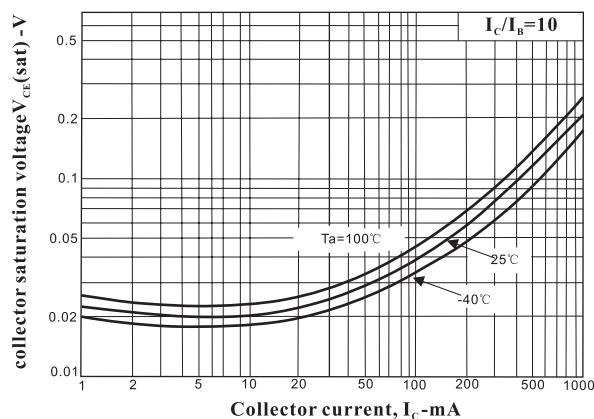
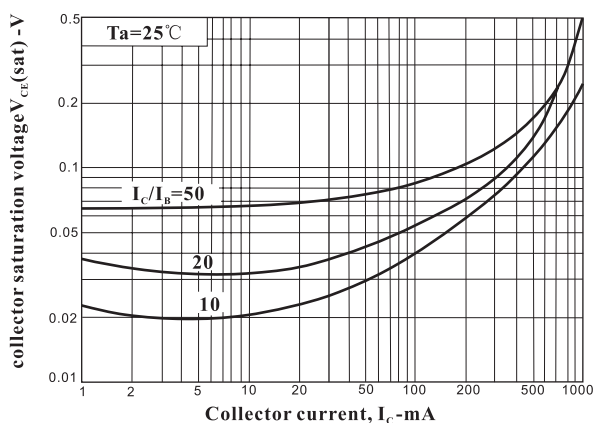
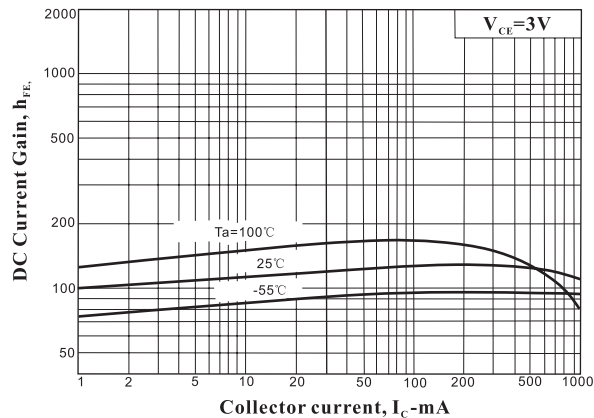
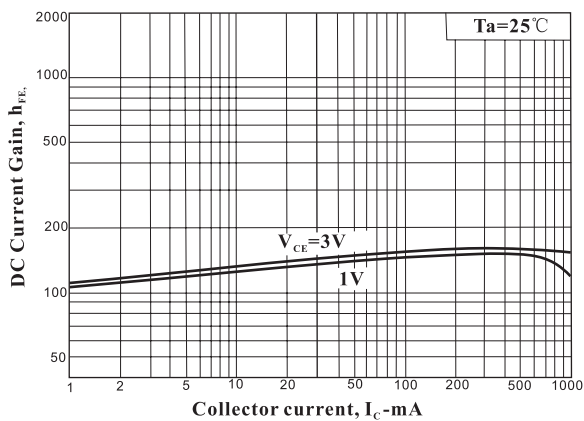
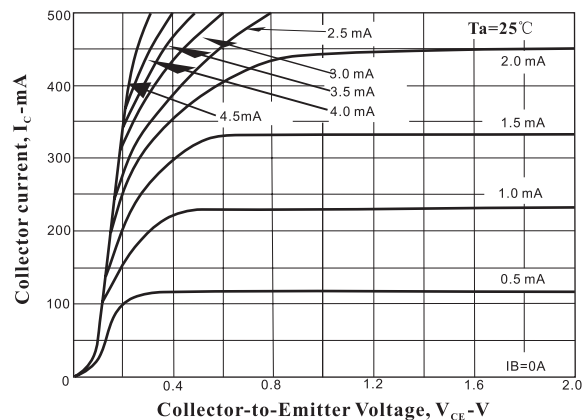
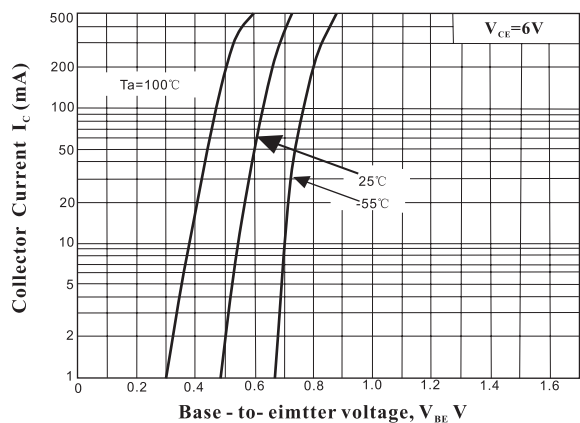
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V _{CB0}	I _c = 50 μA, I _E = 0	40			V
Collector- emitter breakdown voltage	V _{CEO}	I _c = 1 mA, I _B = 0	32			
Emitter - base breakdown voltage	V _{EB0}	I _E = 50 μ A	5			
Collector-base cut-off current	I _{CB0}	V _{CB} = 20 V, I _E = 0			0.5	uA
Emitter cut-off current	I _{EB0}	V _{EB} = 4V, I _c =0			0.5	
Collector-emitter saturation voltage	V _{CE(sat)}	I _c =500 mA, I _B =50mA		0.15	0.4	V
DC current gain	h _{FE}	V _{CE} = 3V, I _c = 100mA	82		390	
Collector output capacitance	C _{ob}	V _{CB} = 10V, I _E = 0,f=1MHz		15		pF
Transition frequency	f _T	V _{CE} = 5V, I _c = -50mA,f=100MHz		150		MHz

■ hFE Classification

Type	2SD1664-P	2SD1664-Q	2SD1664-R
Range	82-180	120-270	180-390
Marking	DAP*	DAQ*	DAR*

RATINGS AND CHARACTERISTIC CURVES

■ Typical Characteristics



RATINGS AND CHARACTERISTIC CURVES

■ Typical Characteristics

